



DMN62D2U

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C
	2.0Ω @ Vgs = 5.0V	390mA
60V	2.5Ω @ Vgs = 2.5V	368mA
	4.0Ω @ V _{GS} = 1.8V	309mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Motor controls
- Power-management functions
- Backlighting

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

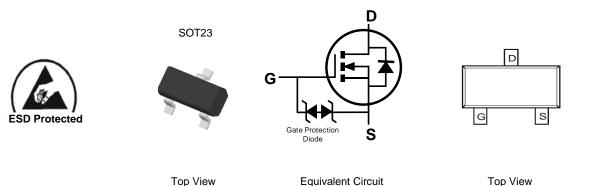
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

 An automotive-compliant part is available under separate datasheet (<u>DMN62D2UQ</u>)

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (c3)
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 4)

Part Number	Baakaga	Packing		
Fait Nulliper	Package	Qty.	Carrier	
DMN62D2U-7	SOT23	3,000	Tape & Reel	
DMN62D2U-13	SOT23	10,000	Tape & Reel	

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

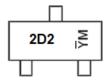
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Notes:



Marking Information



 $\begin{array}{l} \underline{2D2} = Product Type Marking Code\\ \overline{YM} = Date Code Marking\\ \overline{Y} = Year (ex: K = 2023)\\ M = Month (ex: 9 = September) \end{array}$

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	N	0	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	60	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) $V_{GS} = 5.0V$ State $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			ID	390 314	mA
Maximum Continuous Body Diode Forward Current (Note 5)			ls	390	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	6) (Note 5))	Ідм	1.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		PD	0.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	238	°C/W
Total Power Dissipation (Note 5)		PD	0.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	197	°C/W
Operating and Storage Temperature Range	·	T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



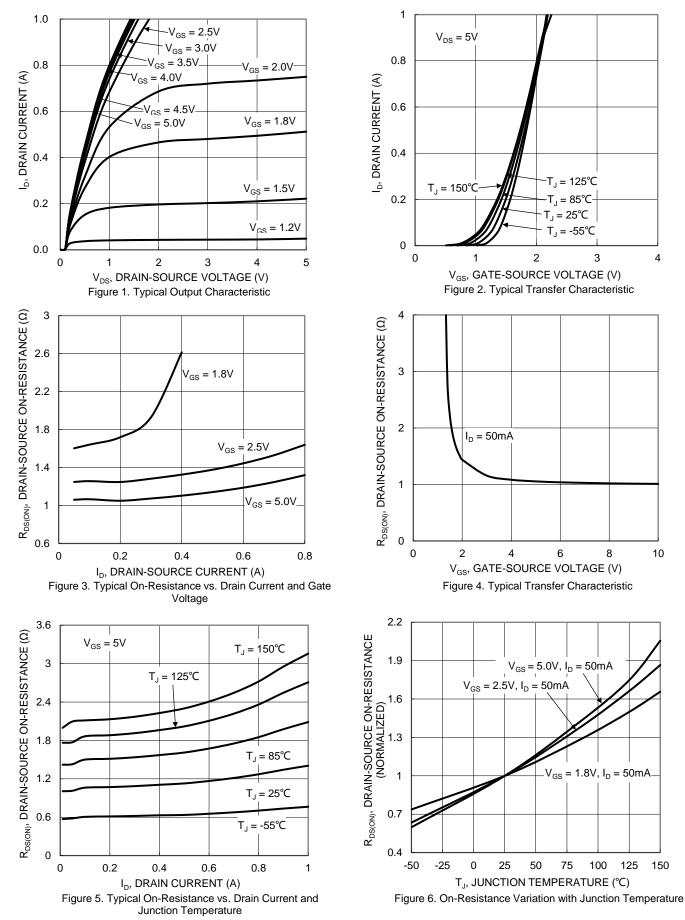
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Cumphiel	Min	True	Max	11	To at Condition	
Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	60	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS			1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_		±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	0.5		1.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
			1.0	2.0		$V_{GS} = 5.0V, I_D = 0.05A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.7 2.1	2.5 4.0	Ω	V _{GS} = 2.5V, I _D = 0.05A	
						V _{GS} = 1.8V, I _D = 0.05A	
Diode Forward Voltage	Vsd		0.7	1.4	V	V _{GS} = 0V, I _S = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)						·	
Input Capacitance	Ciss		41	_	pF		
Output Capacitance	Coss		5.4	_	pF	Vps = 30V, Vgs = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	4.2	_	pF	1 = 1.00012	
Gate Resistance	Rg	_	52	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$	
Total Gate Charge	Qg		0.8	_	nC		
Gate-Source Charge	Qgs		0.2	_	nC	V _{GS} = 4.5V, V _{DS} = 10V Ip = 250mA	
Gate-Drain Charge	Q _{gd}		0.1	_	nC	1D = 23011A	
Turn-On Delay Time	tD(ON)		1.5		ns		
Turn-On Rise Time	tR	_	9.7	_	ns	V _{DD} = 30V, V _{GS} = 10V	
Turn-Off Delay Time	tD(OFF)	_	22.6	_	ns	$R_G = 25\Omega, I_D = 200 mA$	
Turn-Off Fall Time	tF	_	19.5	_	ns		

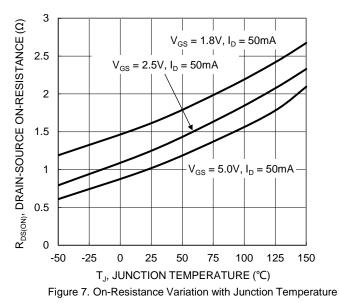
7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing. Notes:

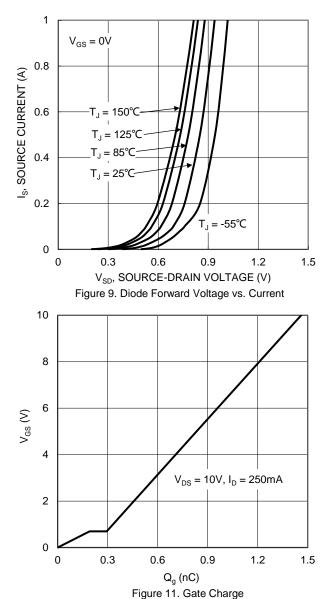


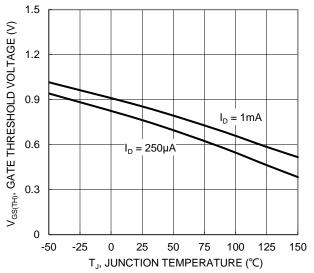
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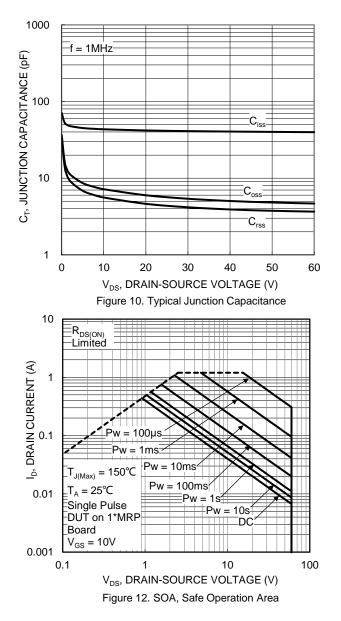




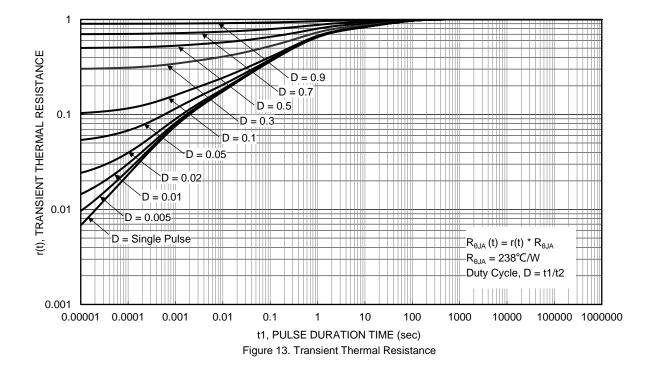








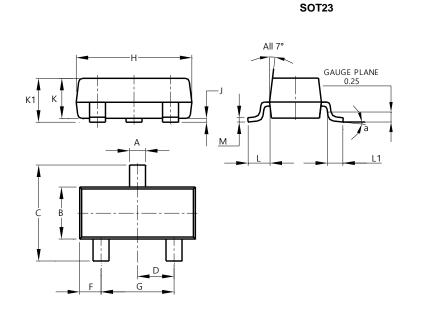






Package Outline Dimensions

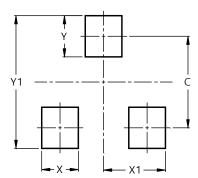
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
в	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
Μ	0.085	0.150	0.110					
а	0°	8°						
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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